

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	650mΩ@-4.5V	-0.66A
	850mΩ@-2.5V	



合肥矽普半导体

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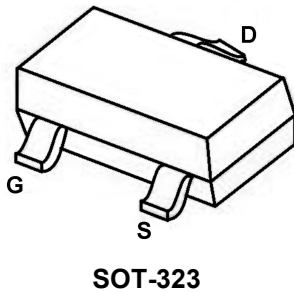
Feature

- High power and current handing capability
- Surface mount package
- ESD protected 2KV

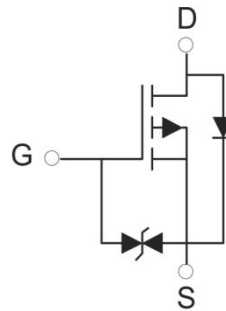
Application

- Battery Switch
- DC/DC Converter

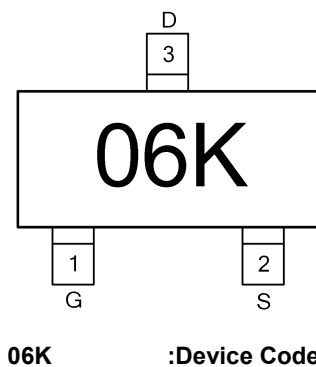
Package



Circuit diagram



Marking



Order Information

Device	Package	Unit/Tape
SP2006KT3	SOT-323	3000

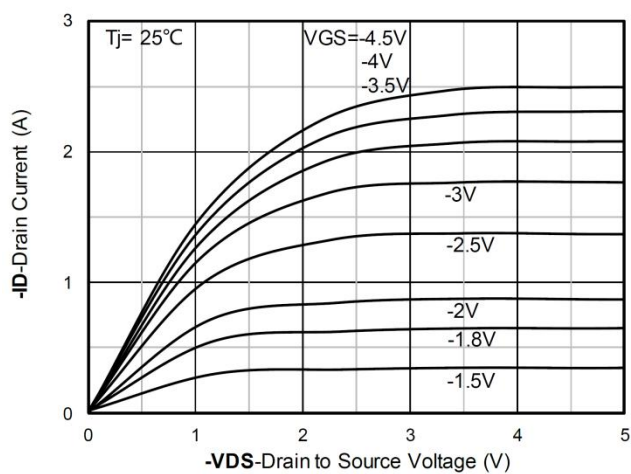
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-0.66	A
Pulse Drain Current Tested	I_{DM}	-2.64	A
Power Dissipation	P_D	200	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	625	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

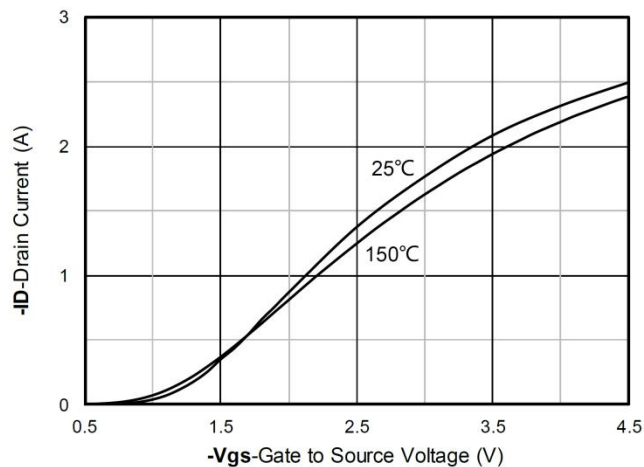
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=-250μA	-20	-	-	V
Drain-Source Leakage Current	IDSS	VDS=-16V , VGS=0V	-	-	-1	uA
Gate-Source Leakage Current	IGSS	VGS=±12V , VDS=0V	-	-	±10	uA
Gate Threshold Voltage	VGS(th)	VDS=VGS , ID=-250μA	-0.35	-0.65	-1.00	V
Static Drain-Source On-Resistance	RDS(on)	VGS=-4.5V , ID=-500mA	-	650	750	mΩ
		VGS=-2.5V , ID=-200mA	-	850	1000	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=-10V , VGS=0V , f=1MH	-	75	-	pF
Output Capacitance	Coss		-	20	-	
Reverse Transfer Capacitance	Crss		-	14	-	
Total Gate Charge	Qg	VDS=-10V , VGS=-4.5V , ID=-0.5A	-	1.25	-	nC
Gate-Source Charge	Qgs		-	0.35	-	
Gate-Drain Charge	Qgd		-	0.27	-	
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=-10V VGS=-4.5V , RG=3Ω , RL=2.5Ω	-	5	-	nS
Turn-On Rise Time	tr		-	19	-	
Turn-Off Delay Time	td(off)		-	15	-	
Turn-Off Fall Time	tf		-	24	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=-1A , TJ=25℃	-	-	-1.2	V

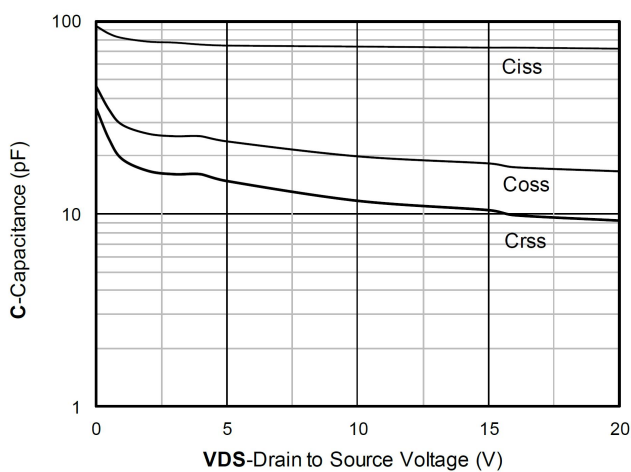
Typical Characteristics



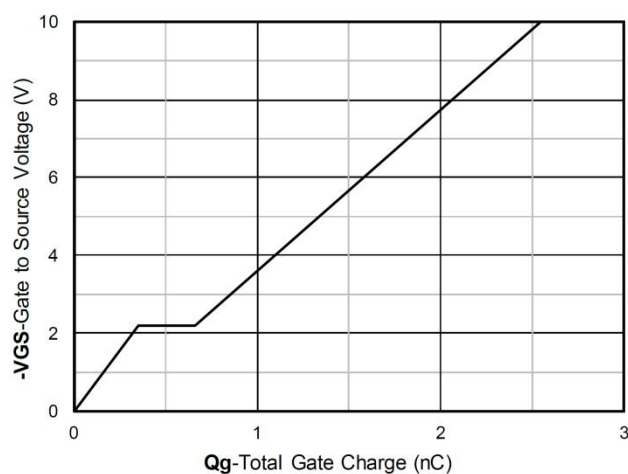
Output Characteristics



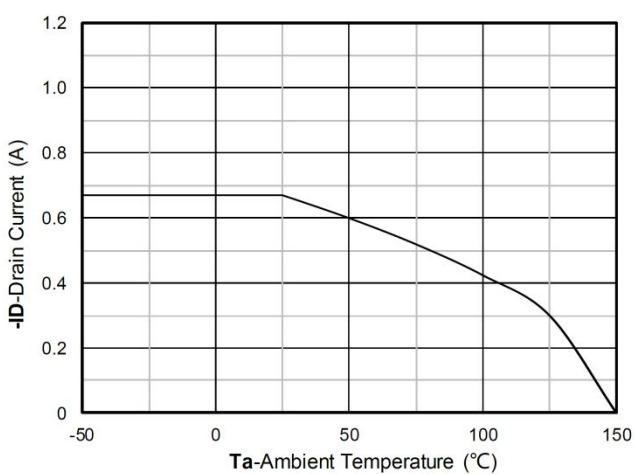
Transfer Characteristics



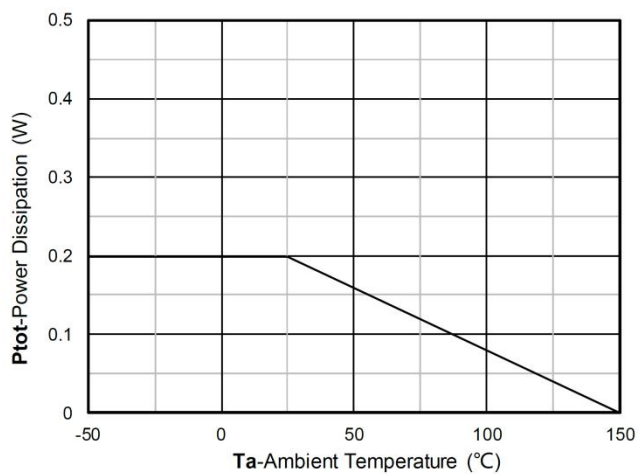
Capacitance Characteristics



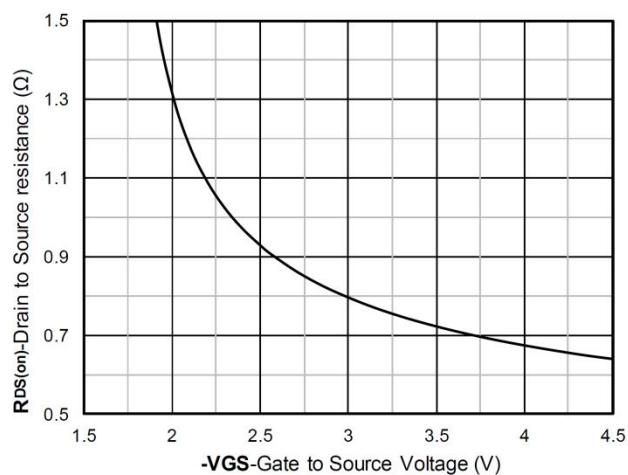
Gate Charge



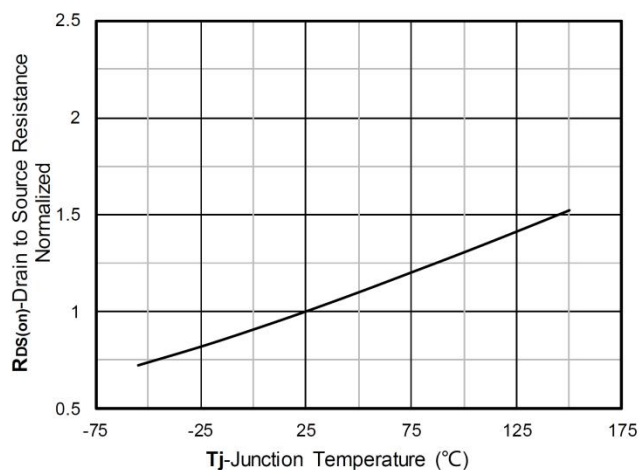
Current dissipation



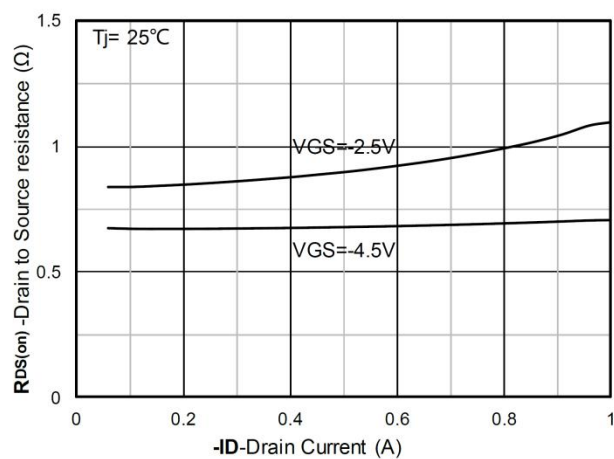
Power dissipation



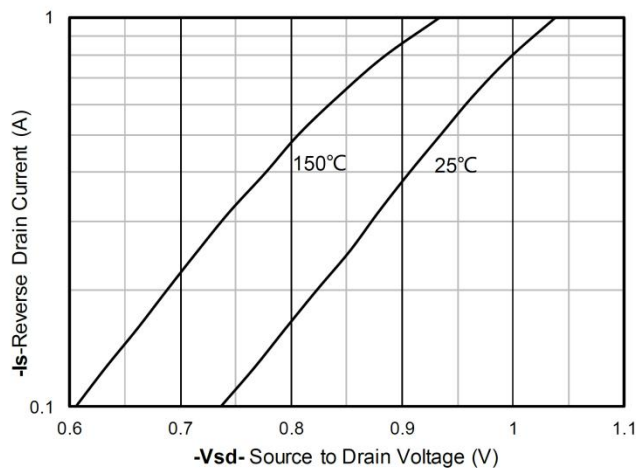
On-Resistance vs Gate to Source Voltage



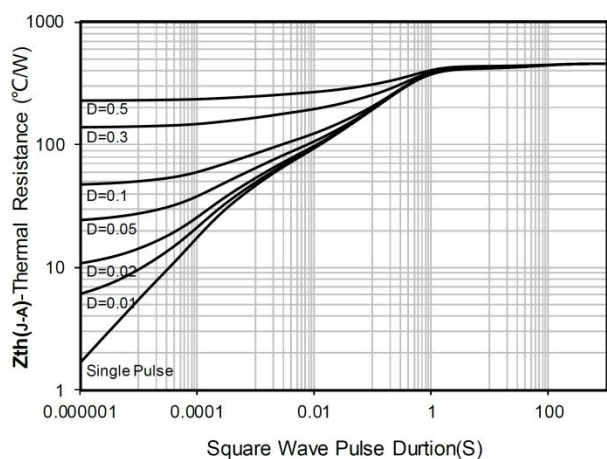
Normalized On-Resistance



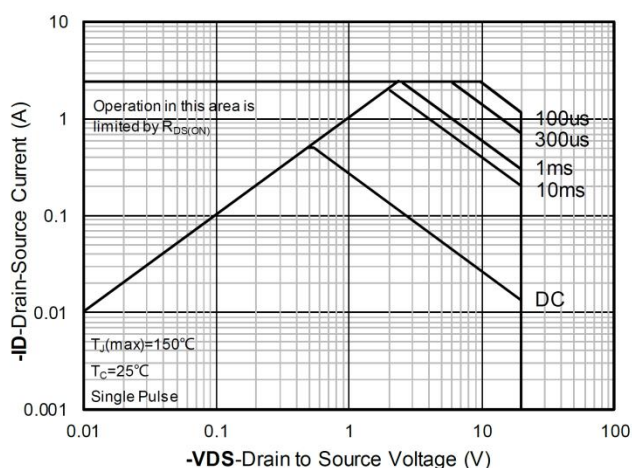
RDS(on) VS Drain Current



Forward characteristics of reverse diode

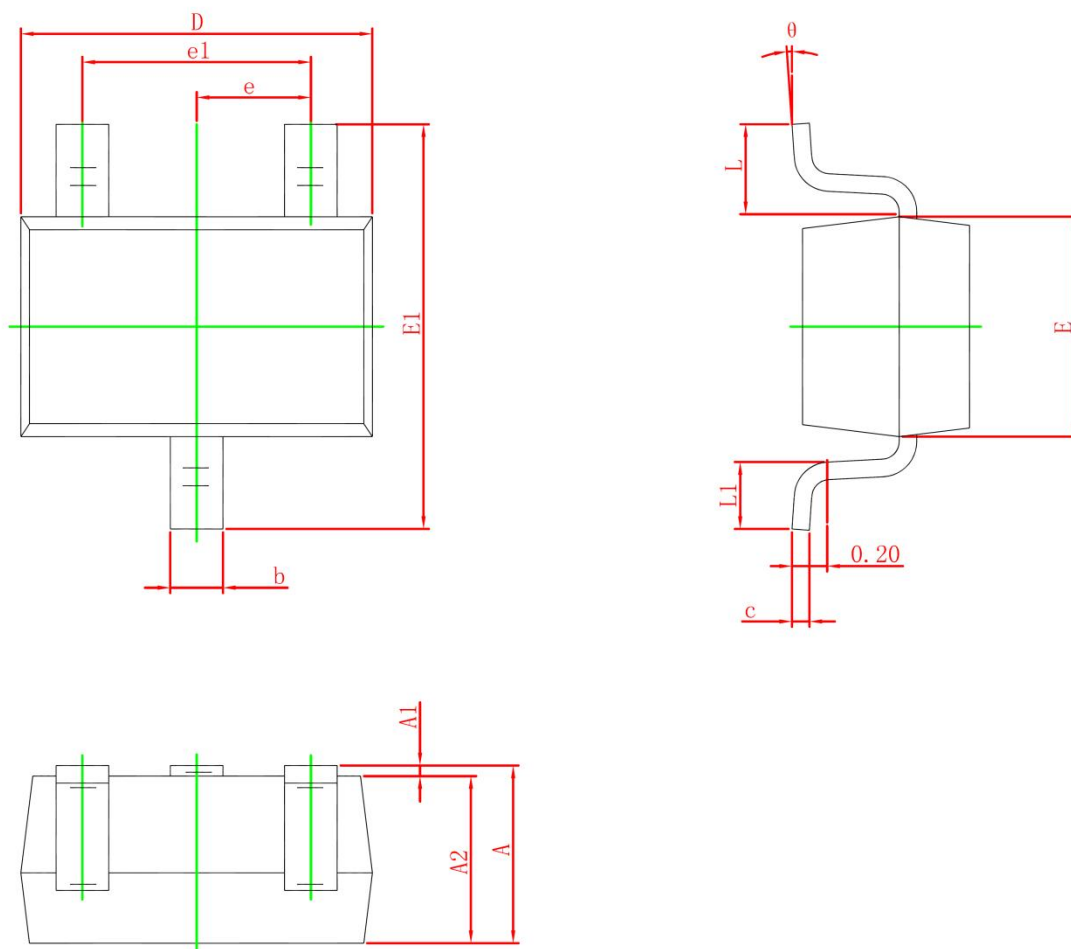


Maximum Transient Thermal Impedance



Safe Operation Area

SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°